

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims, including those in the First Preliminary Amendment, in the application:

Listing of Claims:

Claim 1 (currently amended): A nickel alloy sputtering target for forming a film for preventing Sn diffusion, comprising: 1 to 30at% of Cu; 2 to 25at% of at least one element selected from among V, Cr, Al, Si, Ti and Mo; remnant Ni and unavoidable impurities ~~so as to inhibit the Sn diffusion between a solder bump and a substrate layer or a pad.~~

Claim 2 (currently amended): The nickel alloy sputtering target according to claim 1, wherein the nickel alloy is formed by adding said at least one element selected from among V, Cr, Al, Si, Ti and Mo to a Ni-Cu solid solution.

Claim 3 (canceled).

Claim 4 (original): A nickel alloy thin film formed between a solder bump and a substrate layer or a pad, and comprising 1 to 30at% of Cu; 2 to 25at% of at least one element selected from among V, Cr, Al, Si, Ti and Mo; remnant Ni and unavoidable impurities.

Claim 5 (currently amended): The nickel alloy thin film formed between a solder bump and a substrate layer or a pad according to claim 4, wherein the nickel alloy is formed by adding said at least one element selected from among V, Cr, Al, Si, Ti and Mo to a Ni-Cu solid solution.

Claims 6-8 (canceled).

Claim 9 (new): A nickel alloy thin film according to claim 5, wherein the solder bump is a Pb-free Sn solder or a Sn solder.

Claim 10 (new): A nickel alloy thin film according to claim 9, further comprising a Cu-Sn intermetallic compound layer between the solder bump and the substrate layer or pad.

Claim 11 (new): A nickel alloy thin film according to claim 10, wherein said Cu-Sn intermetallic compound layer is of a thickness of 0.01 to 5 μ m.

Claim 12 (new): A nickel alloy thin film according to claim 4, wherein the solder bump is a Pb-free Sn solder or a Sn solder.

Claim 13 (new): A nickel alloy thin film according to claim 12, further comprising a Cu-Sn intermetallic compound layer between the solder bump and the substrate layer or pad.

Claim 14 (new): A nickel alloy thin film according to claim 13, wherein said Cu-Sn intermetallic compound layer is of a thickness of 0.01 to 5 μ m.

Claim 15 (new): A nickel alloy thin film according to claim 4, further comprising a Cu-Sn intermetallic compound layer between the solder bump and the substrate layer or pad.

Claim 16 (new): A nickel alloy thin film according to claim 15, wherein said Cu-Sn intermetallic compound layer is of a thickness of 0.01 to 5 μ m.

Claim 17 (new): The nickel alloy sputtering target according to claim 2, further comprising Ti, wherein a total amount of Ti together with said at least one element selected from among V, Cr, Al, Si and Mo is 2 to 25at%.

Claim 18 (new): The nickel alloy sputtering target according to claim 1, further comprising Ti, wherein a total amount of Ti together with said at least one element selected from among V, Cr, Al, Si and Mo is 2 to 25at%.